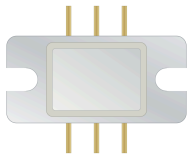
5000–6000 MHz GaN Packaged Power Amplifier — PSAT 49 dBm (typical)

LCI-PA-5000-6000-PS49T · 5000–6000 MHz · GaN Packaged Power Amplifier.



The RF table specifies: PSAT 49 dBm (typical); Power gain 26 dB (typical); PAE 53 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 23 dBm; PW = 100 µs; D = 10%.

CMW010B

Apply gate bias before drain bias. Remove drain bias before gate bias.

Vg: C = 10 µF

Vg: 1, 3

RFin: 2

Vd: 4, 6

RFout: 5

Package outline dimensions: 18.03 × 8.7 mm.

RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 23 dBm; PW = 100 µs; D = 10%

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	5000	-	6000	MHz
Saturated output power	-	48.5	49	-	dBm
Power gain	-	25.5	26	-	dB
Power-added efficiency	-	51	53	-	%
Power-gain flatness	-	-	-	1	dB
Small-signal gain	-	35	36	37	dB
Small-signal gain flatness	-	-	-	±1.5	dB
Input VSWR	-	-	1.8	2	-

DC bias and current

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Drain voltage	-	-	-	-	28	V
Gate voltage	-	-	-	-	-2.8	V
Quiescent current	-	-	-	-	2.1 (Vd = 28 V)	A

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	-	-	-	32	V
Minimum gate bias	-	-5	-	-	V
Storage temperature	-	-65	-	150	°C
Maximum input power	-	-	-	30	dBm
Maximum channel temperature	-	-	-	200	°C

Package outline dimensions

Parameter	Value	Unit
Package outline dimensions	18.03 × 8.7	mm
Terminal span	14.7	mm

Current publication record · 1.6 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.5.

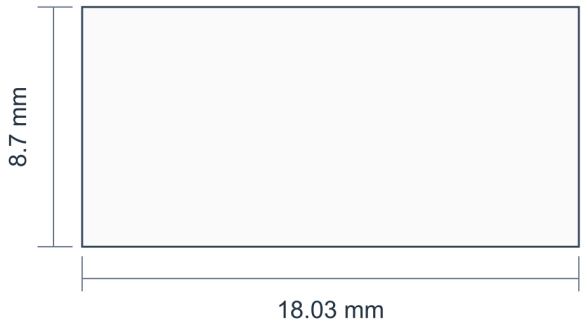
Integration notes

CMW010B Apply gate bias before drain bias. Remove drain bias before gate bias. Vg: C = 10 µF Vg: 1, 3 RFin: 2 Vd: 4, 6 RFout: 5

Mechanical Outline

Partial drawing showing confirmed dimensions in mm. Use the complete installation drawing for installation.

LCI-PA-5000-6000-PS49T



18.03 × 8.7 mm

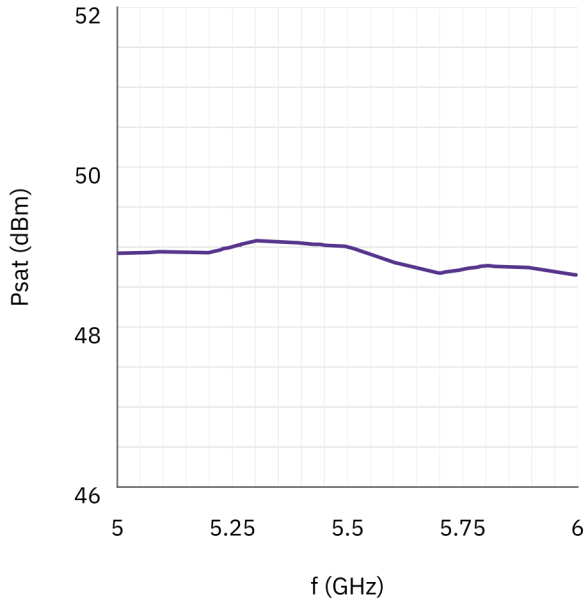
mm

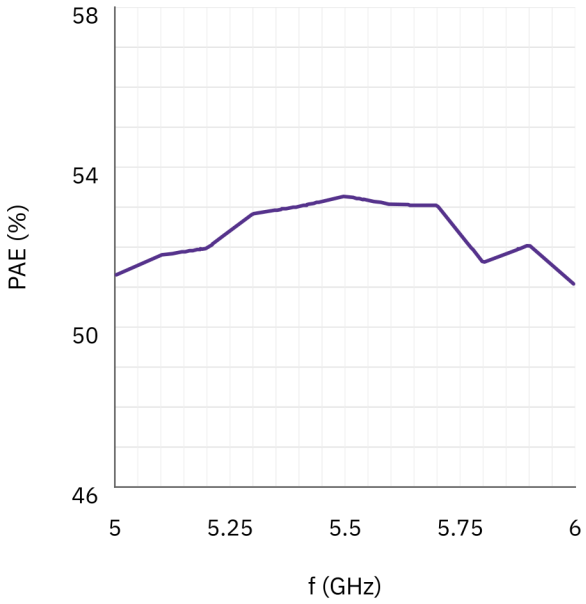
Performance curves

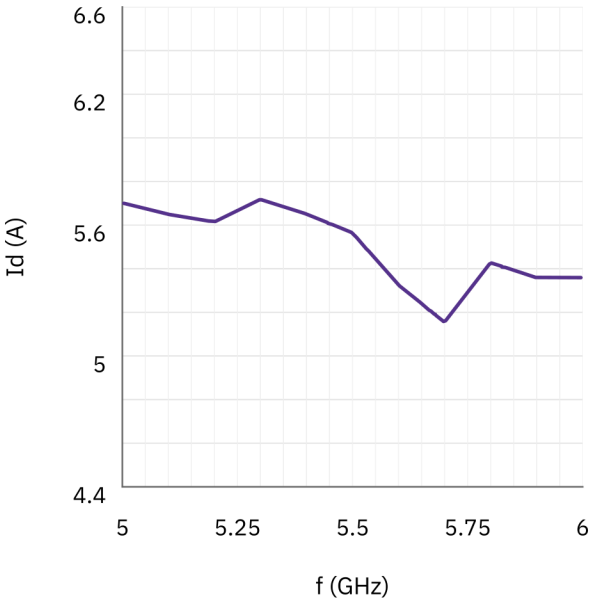
Each performance plot applies to its stated operating conditions.

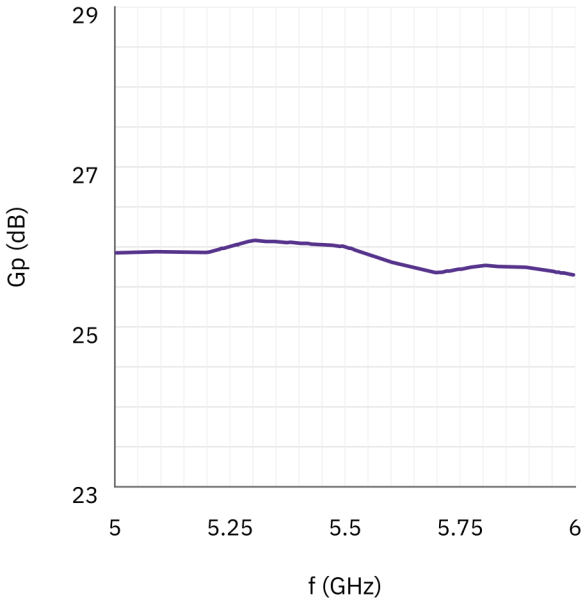
Power-added efficiency; Saturated output power; Dynamic drain current; Power gain.

Readings are approximate. Figure notes: TA = +25 °C; Vd = +28 V; Vg = −2.8 V; Pin = 23 dBm. Pulse width = 100 µs; duty cycle = 10%.









Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.